



K. Memory (Design & Process Technology) 분과

2021년 1월 28일(목), 14:45-16:15 / 채널 D

[TD4-K] Ferroelectric Memory

좌장: 백승재 교수 (한경대학교), 전상훈 교수 (KAIST)

<p>TD4-K-1 14:45-15:15</p>	<p>[초청] Reliability Problem and Improvement Strategy of Ferroelectric Memory Device Jong-Ho Bae <i>School of Electrical Engineering, Kookmin University</i></p>
<p>TD4-K-2 15:15-15:30</p>	<p>Memory Window Enhancement Effect in Metal-ferroelectric-insulator-semiconductor Capacitor with High-k Dielectrics Yeriaron Kim^{1,2}, Seung Youl Kang¹, Jiyong Woo³, Jeong Hun Kim¹, Jong-Pil Im¹, Sung-Min Yoon², and Seung Eon Moon¹ ¹ETRI, ²Kyung Hee University, ³Kyungpook National University</p>
<p>TD4-K-3 15:30-15:45</p>	<p>The Effect of Metal Electrodes on Hafnia Based Ferroelectricity Yongsun Lee, Youngin Goh, Junghyeon Hwang, and Sanghun Jeon <i>School of Electrical Engineering, KAIST</i></p>
<p>TD4-K-4 15:45-16:00</p>	<p>Self-selective Ferroelectric Random Access Memory based on Graphene Field Effect Transistor Sungchul Jung¹, Jinyoung Park², Junhyung Kim³, Wonho Song², Jaehyeong Jo², Seok-Hyung Kang⁴, Muhammad Sheeraz⁵, Tae-Heon Kim⁵, and Kibog Park^{2,3} ¹SK Hynix Inc., ²Department of Physics, UNIST, ³Department of Electrical Engineering, UNIST, ⁴Department of Electrical Engineering, POSTECH, ⁵Department of Physics, University of Ulsan</p>
<p>TD4-K-5 16:00-16:15</p>	<p>The Effect of TiN Top and Bottom Electrodes on the Ferroelectric Properties of Hf_{0.5}Zr_{0.5}O₂ Thin Films Hyo Jeong Kim¹, Yong Chan Jung², Jaidah Mohan², Jeong Gyu Yoo¹, Young In Kim¹, Yonghwan An¹, Jiyoung Kim², and Si Joon Kim¹ ¹Department of Electrical and Electronics Engineering, Kangwon National University, ²Department of Materials Science and Engineering, The University of Texas at Dallas</p>